

Re-entrant resonant tunneling

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Abstract

We study the effect of electron–electron interactions on the resonant–tunneling spectroscopy of the localized states in a barrier. Using a simple model of three localized states, we show that, due to the Coulomb interactions, a *single* state can give rise to *two* resonant peaks in the conductance as a function of gate voltage, $G(V_g)$. We also demonstrate that an additional higher–order resonance with V_g –position in between these two peaks becomes possible when interactions are taken into account. The corresponding resonant–tunneling process involves two–electron transitions. We have observed both these effects in GaAs transistor microstructures by studying the time evolution of three adjacent $G(V_g)$ peaks caused by fluctuating occupation of an isolated impurity (modulator). The heights of the two stronger peaks exhibit in–phase fluctuations. The phase of fluctuations of the smaller middle peak is opposite. The two stronger peaks have their origin in the same localized state, and the third one corresponds to a co–tunneling process.

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Resonant tunneling through localized states in an insulating barrier (RT) has been observed in several types of semiconductor structures. It occurs when the energy of tunneling electrons is close to the energy of a localized state (LS). If a LS resides near the midpoint of the barrier its contribution to the conductance is of the order of e^2/h . In the first experiments on diode structures^{1–3} the barrier represented a planar oxide layer sandwiched between two metallic contacts. In the later experiments^{4–6} a *GaAs* quantum well with LS's in it was separated from the contacts by two *AlGaAs* barriers. On small area barriers the authors were able to resolve the tunneling through individual LS's occurring at resonant bias voltages.

Another group of experiments was carried out using lateral semiconductor structures^{7–9} with a two-dimensional electron gas. The barrier between the contacts is created by depleting electrostatically the region under the gate. The advantage of such a geometry is that the energy position of a LS with respect to the Fermi level in the contacts can be varied by changing the gate voltage V_g . As V_g is swept, different LS's in the barrier align with the Fermi level. As a result, narrow peaks are seen in the V_g dependence of the ohmic conductance G . The fact that the shape of these peaks remains unchanged with decreasing temperature allows resonant tunneling to be distinguished from the phonon-assisted transport⁷. The magnitude of a conductance peak is determined by the well-known formula

$$G_{max} = \frac{e^2}{h} \frac{4\Gamma_l\Gamma_r}{(\Gamma_l + \Gamma_r)^2}, \quad (1)$$

where Γ_l and Γ_r are the tunneling widths of the LS associated with electron escape into the left and right contacts respectively. Since Γ_l, Γ_r depend exponentially on the location of the LS within the barrier, the measurement of the $G(V_g)$ dependence can be viewed as a resonant-tunneling spectroscopy of localized states in the barrier: the V_g positions of the peaks reflect the energies of LS's, while their magnitudes characterize the spacial positions of LS's with respect to the center of a barrier.

Such a spectroscopy implies that LS's are well separated in the direction along the barrier (y -direction in Fig. 1). Otherwise, the Coulomb interaction between different LS's becomes important. Due to this interaction, the energy position of a LS, as revealed in $G(V_g)$ dependence, becomes a function of the occupation of the neighboring LS's. To illustrate this, consider two LS's with energies ε_1 and ε_2 (Fig. 1). Since $\varepsilon_1 < \varepsilon_2$ the level ε_1 is the first to “resonate” as the Fermi level in the contacts, μ , moves up with increasing V_g . For $\mu > \varepsilon_1$ the level ε_1 becomes occupied. This causes an upward Coulomb shift, U_{12} , of the second LS. As a result the occupation number of the second LS will change from 0 to 1 not at $\mu = \varepsilon_2$ but at $\mu = \varepsilon_2 + U_{12}$. However, as long as the two-LS's configuration is considered, one can still attribute each peak in $G(V_g)$ to an individual LS. In the present paper we demonstrate that, in general, this is not the case. Namely we will show that due to the Coulomb interactions a *single* LS can cause *two peaks* in $G(V_g)$ dependence. We call this effect (resonant tunneling through the same LS at two different positions of μ) re-entrant resonant tunneling. We will then present the experimental evidence for this effect in *GaAs* transistor microstructures.

Consider a configuration consisting of three LS's with energies $\varepsilon_1, \varepsilon_2$ and ε_3 (Fig. 1(a)). Let us trace the evolution of their occupation numbers with μ moving upwards. At $\mu = \varepsilon_1 = \mu_1$ the first LS becomes occupied. As already discussed, the second LS changes its occupation at $\mu = \varepsilon_2 + U_{12} = \mu_2$. Both charged LS's produce the Coulomb shifts, U_{23}

and U_{13} of the third LS so that with further increasing μ the third LS gets charged at $\mu = \varepsilon_3 + U_{13} + U_{23} = \mu_3$. If, as it is shown in Fig. 1(a), only the first LS is close to the center of the barrier, while the other two are displaced towards the left and the right boundaries, one should expect one strong peak and two weak peaks in $G(V_g)$. Note, however, that for above scenario to apply one should verify that after the charging of the third LS the energies of the first and the second LS still remain below the Fermi level. Indeed for $\mu > \mu_3$ these energies acquire positive shifts U_{13} and U_{23} respectively. For the first LS the corresponding condition $\mu_1 + U_{12} + U_{13} < \mu_3$ can be rewritten as

$$\varepsilon_3 - \varepsilon_1 > U_{12} - U_{23}. \quad (2)$$

This condition can be violated if the first and the third LS are close enough in energy. Then the question arises: what would the evolution of the occupation numbers be in this case? Note first that the meaning of inequality (2) is that the total energy of two electrons in the system of three LS's is minimal when they occupy the first and the second LS. This energy is equal to $\varepsilon_1 + \varepsilon_2 + U_{12}$. Consequently, the reversed inequality means that the minimum energy for the two electrons corresponds to the occupation of the second and the third LS and is equal to $E_2 = \varepsilon_2 + \varepsilon_3 + U_{23}$. If this is the case then the process of the charging of the system will go as follows. At $\mu = \mu_1$ the first LS gets charged. At $\mu = \varepsilon_2 + \varepsilon_3 + U_{23} - \varepsilon_1 = \mu^*$ we have $\varepsilon_1 + \mu^* = E_2$. At this position of the Fermi level an electron from one of the contacts and an electron from the first LS occupy the second and the third LS, leaving the first LS empty. (Note that this position of the Fermi level is lower than that required to charge just the second LS, since $\mu^* < \mu_2$ if the condition (2) is violated.) Finally, the first LS *will be charged again* at $\mu = \varepsilon_1 + U_{12} + U_{13} > \mu^*$.

From the evolution of the occupation numbers described above one should anticipate two strong resonant-tunneling peaks in $G(V_g)$: at $\mu = \varepsilon_1$ and at $\mu = \varepsilon_1 + U_{12} + U_{23}$ corresponding to the resonance of the first LS. Note however, one more resonant-tunneling process is possible at an intermediate value of μ , namely at $\mu = \mu^*$. The “resonating” states are the states of two electrons. They are:

- (i) initial: an electron at the Fermi level in the left contact and electron on the first LS,
- (ii) intermediate: one electron on the second and another on the third LS,
- (iii) final: an electron at the Fermi level in the right contact and electron on the first LS.

All three energies are equal at $\mu = \mu^*$. It can be shown that for such a process the magnitude of the peak in the conductance is still given by Eq. (1), but the values of Γ_l and Γ_r are now determined by *two-electron* transitions in the following way.

One can write the general expressions for both widths: $\Gamma_l = \pi|V_l|^2g$, $\Gamma_r = \pi|V_r|^2g$, where g is the density of states in the contacts and V_l , V_r are the corresponding matrix elements. In the case of the resonant tunneling through the first LS one has $V_l = V_0 \exp(-\frac{R_{1l}}{a})$, $V_r = V_0 \exp(-\frac{R_{1r}}{a})$, where a is the localization radius, R_{1l} , R_{1r} are the distances from the first LS to the left and to the right contacts respectively, and V_0 is the prefactor. Then the formula (1) for G_{max} takes the form

$$G_{max} = \frac{e^2}{h} \cosh^{-2} \left(\frac{R_{1l} - R_{1r}}{a} \right). \quad (3)$$

For the two-electron transition between the states (i) and (ii) the matrix element $\tilde{V}_l$ can be presented as

$$\tilde{V}_l = V_0 \exp\left(-\frac{R_{l2}}{a}\right) \left[\frac{V_0 \exp(-\frac{R_{13}}{a})}{\mu^* - \varepsilon_2 - U_{12}} + \frac{V_0 \exp(-\frac{R_{13}}{a})}{\varepsilon_1 - \varepsilon_3} \right], \quad (4)$$

where R_{l2} is the distance from the second LS to the left contact and R_{13} is the distance between the first and the third LS's. Two terms in the matrix element (4) reflect the fact that two steps of the transition can be carried out in a different order (and thus through different virtual states). We emphasize that this matrix element is non-zero only due to the interactions. Indeed, it is easy to see that in the absence of the Coulomb shifts two terms in (4) cancel each other out.

The matrix element $\tilde{V}_r$ of the transition between the states (ii) and (iii) has a form similar to (4)

$$\tilde{V}_r = V_0 \exp\left(-\frac{R_{r3}}{a}\right) \left[\frac{V_0 \exp(-\frac{R_{12}}{a})}{\mu^* - \varepsilon_3 - U_{13}} + \frac{V_0 \exp(-\frac{R_{12}}{a})}{\varepsilon_1 - \varepsilon_2} \right], \quad (5)$$

where R_{r3} is the distance from the third LS to the right contact and R_{12} is the distance between the first and the second LS's. Using Eqs. (4), (5) one can find the two-electron widths $\tilde{\Gamma}_l = \pi |\tilde{V}_l|^2 g$, $\tilde{\Gamma}_r = \pi |\tilde{V}_r|^2 g$. Substituting $\tilde{\Gamma}_l$, $\tilde{\Gamma}_r$ into Eq. (1) we obtain the following expression for the maximal conductance

$$\tilde{G}_{max} = \frac{e^2}{h} \cosh^{-2} \left(\frac{R_{l2} + R_{13} - R_{12} - R_{r3}}{a} + \gamma \right), \quad (6)$$

where the dimensionless constant γ is defined as

$$\gamma = \ln \left| \frac{(U_{12} - U_{23})(\varepsilon_2 - \varepsilon_1)(\varepsilon_2 - \varepsilon_1 + U_{23} - U_{13})}{(U_{13} - U_{23})(\varepsilon_3 - \varepsilon_1)(\varepsilon_3 - \varepsilon_1 + U_{23} - U_{12})} \right|. \quad (7)$$

We see that the condition $\tilde{G}_{max} \simeq e^2/h$ has the form $R_{l2} + R_{13} = R_{12} + R_{r3}$, and it can be satisfied even if the first LS is displaced from the center of the barrier, so that G_{max} is small.

The conduction involving virtual states considered here is similar to the elastic co-tunneling process in the Coulomb blockade¹⁰. In co-tunneling, electrons traverse a conducting grain using virtual states when the transition via a real state is forbidden by the charging energy^{10,11}. The main difference is in the number of virtual states. The quasi-continuum of states available in a metallic grain leads to the interference suppression of the co-tunneling rate¹⁰, while such a suppression obviously does not occur in the problem considered here.

To study the effect of the re-entrant RT experimentally, we used sub-micron GaAs MESFETs with lateral barriers^{12,13}. Earlier, on these structures we demonstrated the presence of elementary RT channels in $G(V_g)$ and $I(V)$ characteristics and distinguished between one- and two-impurity RT. This lateral structure with a smooth barrier, Fig. 1, is well suited for testing the discussed model. It has an enhanced density of localized states near the contacts which will not give large peaks in $G(V_g)$ unless two-impurity RT is involved¹³, although a change in the charge of these states with varying V_g can affect the states close to the middle of the barrier. By a standard lock-in technique we have measured the conductance of GaAs MESFETs with a donor concentration of 10^{17} cm^{-3} . Highly doped source-drain contacts have metallic-like conduction. The barrier between the source and drain with localized states in it is produced by a gate of length $L=0.2 \text{ } \mu\text{m}$ in the direction of the current and

width $W=20\text{ }\mu\text{m}$ in the perpendicular direction. The height of the barrier is controlled by the gate voltage which shifts the localized states in the barrier with respect to the Fermi level in the contacts.

The experimental demonstration of the re-entrant resonant tunneling should provide an evidence that the two peaks in $G(V_g)$ have their origin in the same localized state. Firstly, we expect that the heights of these peaks should be similar. (A possible difference in the heights can be due to some effect on the values of Γ_l and Γ_r in (1) when levels 2 and 3 are charged.) Secondly, the external fields should influence both peaks in the same way, if the peaks originate from the same energy level. If this field is a random electric field caused by the occupancy fluctuations of an isolated impurity (modulator), such a modulator can serve as a local probe to the arrangement of localized states in the barrier. To explore this possibility we have measured $G(V_g)$ curves repeatedly for a long period of time (several hours) and analysed the fluctuations of peaks in $G(V_g)$ with time.

Fig. 2 shows an example of $G(V_g)$ at $T=100\text{ mK}$ with the peaks which we associate with one-impurity RT channels. Among a dozen peaks there is a group of three neighbouring peaks labelled A, B and C that have two distinct states at different times. Two-level conductance fluctuations in mesoscopic structures (Random Telegraph Signal) are commonly connected with a single impurity placed close to a conducting path of small size¹⁴. The fluctuations of the occupancy of this impurity produce a random electric field which modulates the conductance of the path. The surprising feature of the fluctuations of the three peaks in Fig. 2 is that these fluctuations are coherent: the decrease of peaks A and C and increase of peak B occur simultaneously. Fig. 3(a) shows the fluctuations of the peak amplitudes with time. Comparison of the relative magnitudes of these fluctuations shows that for the peaks A and C they are very close: G_{high}/G_{low} is 1.52 for peak A and 1.58 for peak C. The fluctuations in the amplitude are accompanied by distinct but less pronounced shifts in the positions of the peaks, Fig. 3(b). We have also found a similar group of three peaks with coherent fluctuations on another sample from the same wafer. The only difference in the second sample is that the fluctuations of the middle peak B, which has the smallest amplitude, are hardly detectable.

The fact that the observed fluctuations of the peak amplitude are simultaneous and have the same relative magnitude suggests that the peaks A and C can be considered as being due to the same LS (state 1 in our model). Let us examine first an alternative explanation where these peaks are due to different LSs. We will see that this straightforward view can be dismissed as highly improbable. Expression (1) for the tunneling peak amplitude can be reduced to $G_{max} = (e^2/h)(\Gamma_{min}/\Gamma_{max}) = (e^2/h)\exp[-(R_{max} - R_{min})/a]$, where $\Gamma_{min}(\Gamma_{max})$ is the minimal (maximal) value of Γ_l, Γ_r and $R_{max}(R_{min})$ is the corresponding distance from the LS to the contacts, Fig.1,b. Similar values of G_{max} for the two peaks means that the other LS has to lie on the same line along the barrier as state 1 (or on the symmetric about the centre line). The equal effect of the modulator on the two states means that their distances to the modulator have to be the same. Thus, for a given state 1 there is only one possible place for the other state to satisfy the experimental facts: at the intercept of the sphere with the modulator in its center, with the line in the 2D plane of the barrier, see Fig. 1(b). The uncertainty in the position of this state in the plane is of the order of a^2 , where a is the localization radius, and in the energy scale it is of the order of Γ_{max} . With an accuracy of a numerical factor, the probability to meet such a localized state P_{1-2} is

$g_{2D}a^2\Gamma_{max}$, where g_{2D} is the two-dimensional density of states. In our structures the value of g_{2D} is about ten times less than the conduction band value $3 \times 10^{10} \text{ cm}^{-2}\text{meV}^{-1}$, and $a \approx 100 \text{ \AA}$. The rate of the Fermi level shift with gate voltage $\alpha = d\mu/deV_g \approx 0.2^{13}$ gives $\Gamma_{max} \approx 0.2 \text{ meV}$ from the width of the peaks in the V_g -scale. For the probability P_{1-2} we then obtain a very small value of 6×10^{-4} .

For the re-entrant tunneling view we have to estimate the probability to meet two states in the vicinity of the first LS. These states should lie within an area of $L_c \times L_c$ for the Coulomb interaction not to be screened by the metallic gate, where L_c is the distance between the gate and the conducting channel (in our structures $L_c \approx 1000 \text{ \AA}$ and is comparable to an effective barrier length). The characteristic energy interval of these two states should be now of the order of the Coulomb energy $U_{ij} \approx e^2/\kappa L_c \approx 1 \text{ meV}$. This value agrees with the estimation of U_{ij} from the separation ΔV_g between peaks A and C in Fig. 2, which in the re-entrant tunneling model is $U_{12} + U_{13} = \alpha e \Delta V_g \approx 1 \text{ meV}$. The probability P_{1-23} to meet the two impurities is then $(g_{2D}U_{ij}L_c^2)^2 \approx 0.1$. The latter is two orders of magnitude larger than the value of P_{1-2} and it is large enough to make the effect of re-entrant tunneling observable.

In our explanation the only feature of the modulator that is important is that it has a local effect on the surrounding localized states. Its most probable position is between the gate and the conducting channel as is indicated in Fig. 1(b). This conclusion is drawn from the fact that we do not see incoherence in the fluctuations of the peaks A and C which are shifted in V_g -scale by $\Delta V_g = 6 \text{ mV}$. It means that this change in V_g does not affect the average occupancy of the modulator. For an energy level under the gate such a change in V_g will indeed have a small effect, as its occupancy is formed under the condition of a strong electric field between the gate and channel, $V_g \approx -1.7 \text{ V}$. The fluctuations of the modulator charge in time can result from a small gate-channel leakage current, as it was seen in¹⁵.

We explain the difference in the amplitudes of peaks A and C by the influence of charged levels 2 and 3 on Γ_{min} and Γ_{max} in the expression for the first level resonance $G_{max} = (e^2/h)(\Gamma_{min}/\Gamma_{max})$. It is interesting to note that the modulator produces a similar change in the peak amplitudes but without significant change in the V_g - position of the peaks (the shift accompanying the amplitude modulation is ten times less than the separation between peaks A and C). Within our model, with the second and the third LSs positioned on the opposite sides of the first LS, this can be understood as follows. Although states 2 and 3 are closer to the state 1 than the modulator and thus produce a stronger Coulomb shift of the energy position of state 1, their effects on Γ_{min} and Γ_{max} are partially compensated in G_{max} which is the ratio of the two values. The modulator, however, is most probably located assymetrically with respect to the first LS and it mainly affects one of the two Γ s, so that the compensation does not occur.

Peak B in Fig. 2 has a much smaller amplitude than peaks A and C. In addition, its modulation is in anti-phase with that of the peaks A and C: the decrease of the peak B corresponds to the increase of the other two. This implies that its origin is not in the state 1. For the states 2 and 3 we would normally expect to see *two* small peaks, unless these states are positioned too far from the middle of the barrier to give a measurable conductance. The presence of only one resonance allows us to suggest that the peak B in Fig. 2 is due to *co-tunneling* with all states 1, 2 and 3 involved. Note that for peaks A and C the modulation results from the change of the ratio Γ_l/Γ_r in (1) by the electric field of the modulator,

whereas for co-tunneling (6) it is the ratio $\tilde{\Gamma}_l/\tilde{\Gamma}_r$ that determines the peak amplitude. It is quite plausible that when one ratio increases the other decreases and vice versa, which would lead to the anti-phase modulation of the co-tunneling peak.

In conclusion, we have demonstrated that charging effects can drastically change the resonant-tunneling spectroscopy of localized states in the barrier. These effects cause the doubling of the single-impurity peaks and also give rise to additional peaks due to many-electron tunneling.

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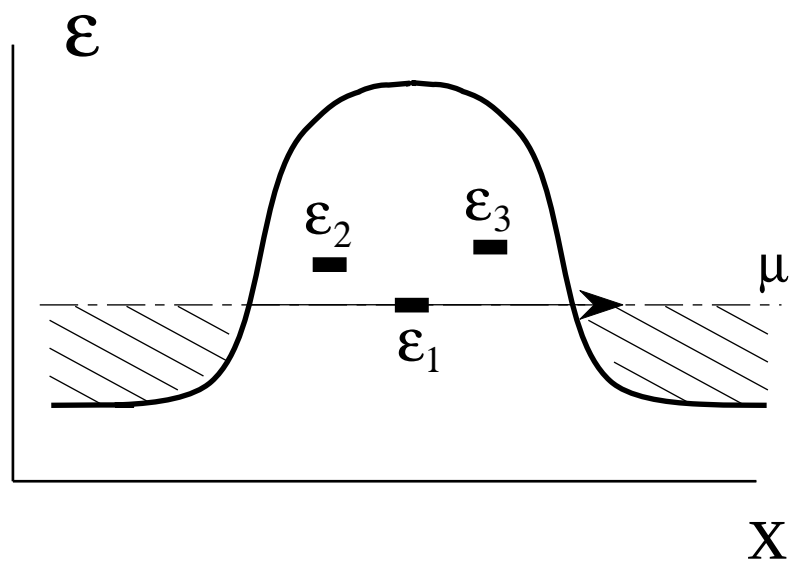
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FIGURES

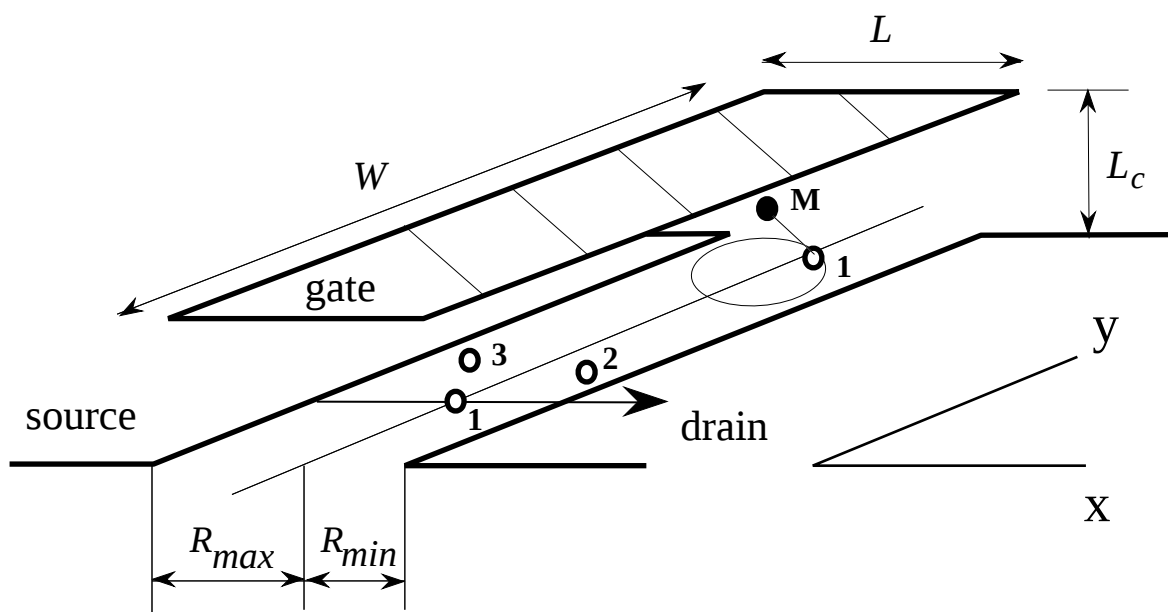
FIG. 1. a) Schematic diagram of the barrier with resonant tunneling through the first localized state (states 2 and 3 are not occupied). b) Spatial position of the localized states and a modulator in the potential barrier under the gate. The part with the state 1 and modulator M illustrates the estimation of the probability for the peak C to be due to an independent localized state. The part with three localized states (1,2 and 3) corresponds to the probability to meet three interacting states.

FIG. 2. Two consecutive measurements of the ohmic conductance as a function of gate voltage. Peaks A,B and C show fluctuations between distinct two states while the neighbouring peaks are time independent.

FIG. 3. a) Fluctuations of the amplitude of peaks A,B and C with time. b) Fluctuations of the positions of these peaks in V_g -scale accompanying the amplitude fluctuations. The peak D at $V_g = -1.734$ V is the neighbour of peak C and it does not show coherent fluctuations.



a)



b)

Fig.1

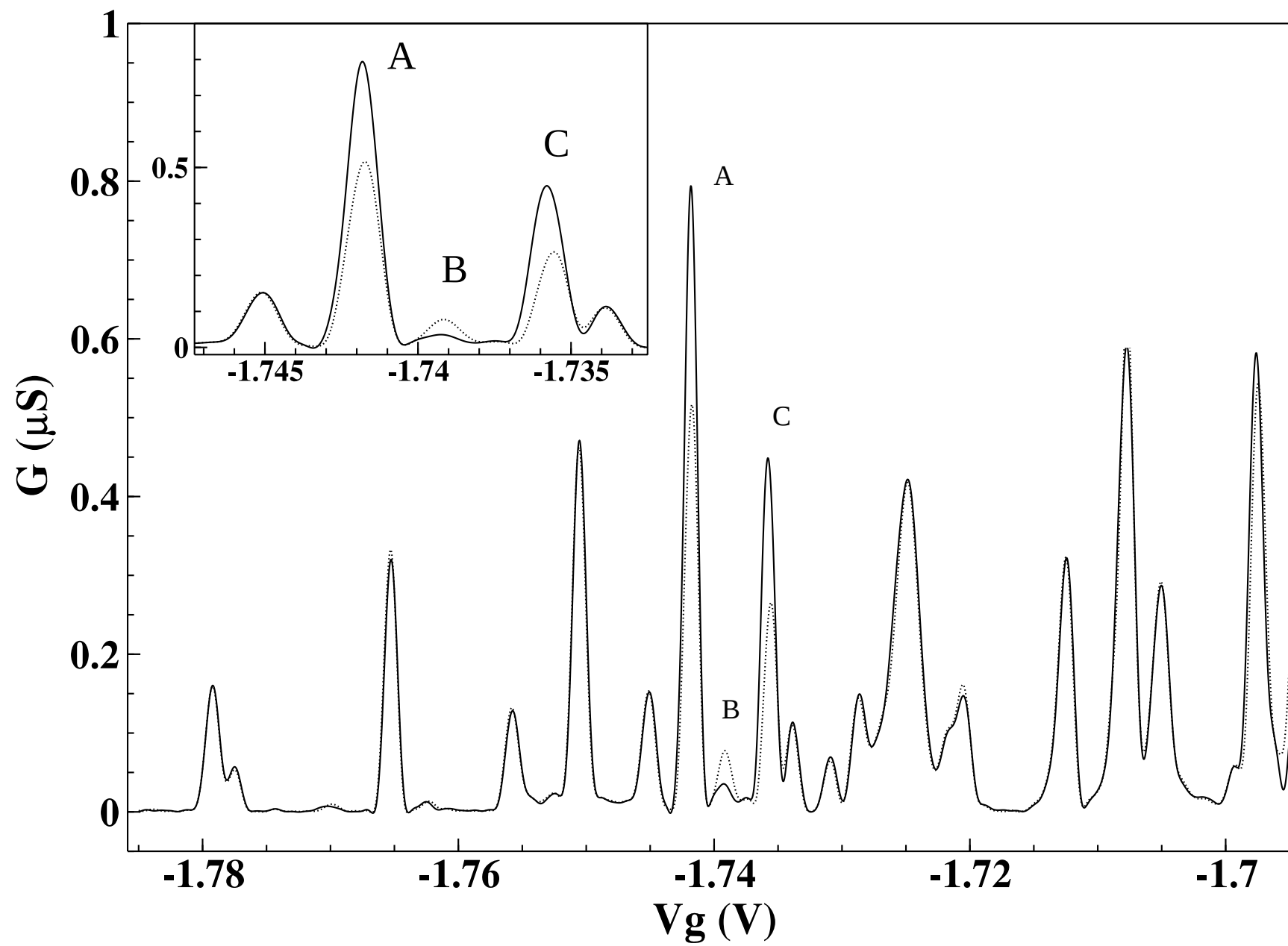


Fig.2

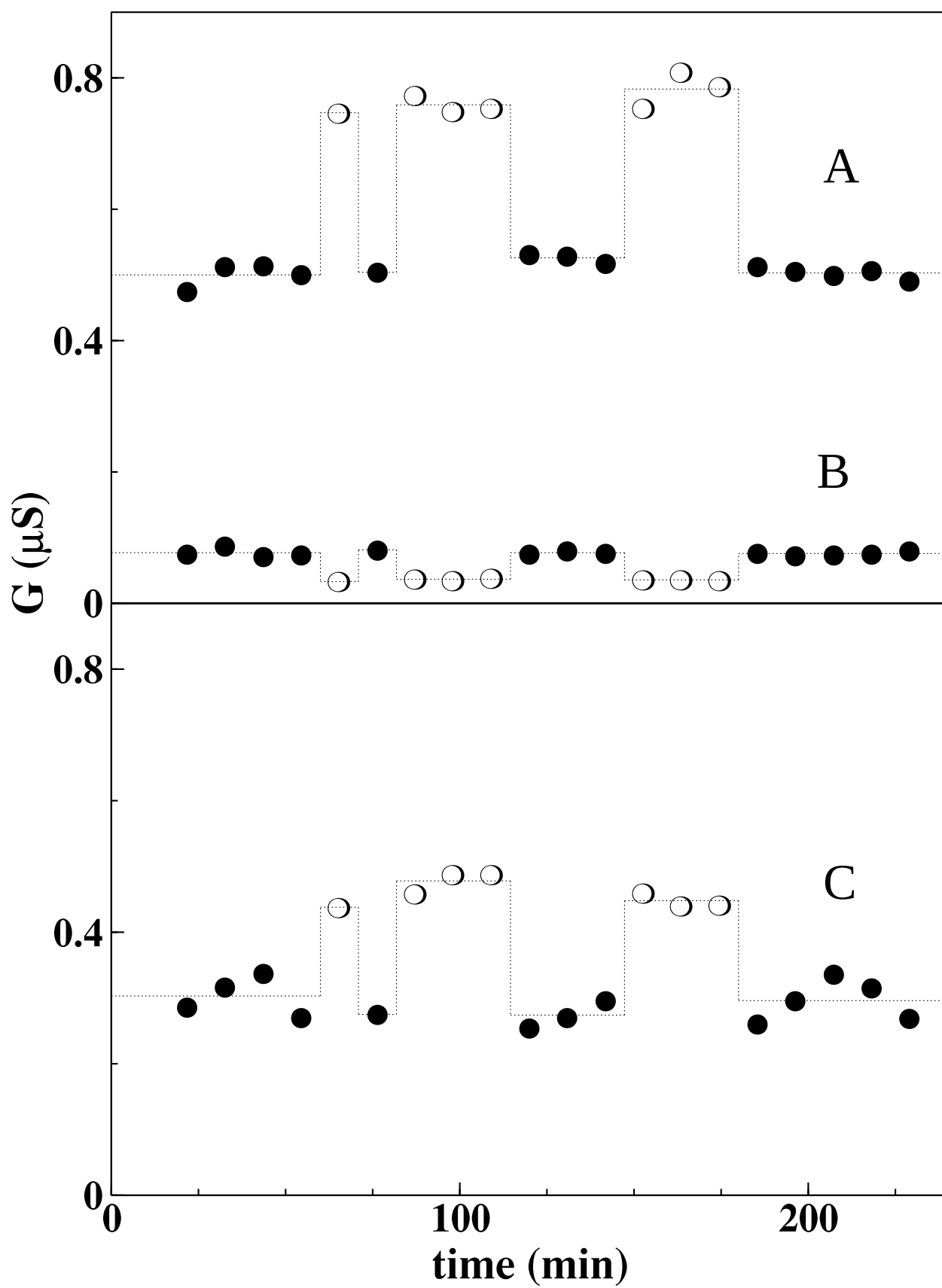


Fig.3, a

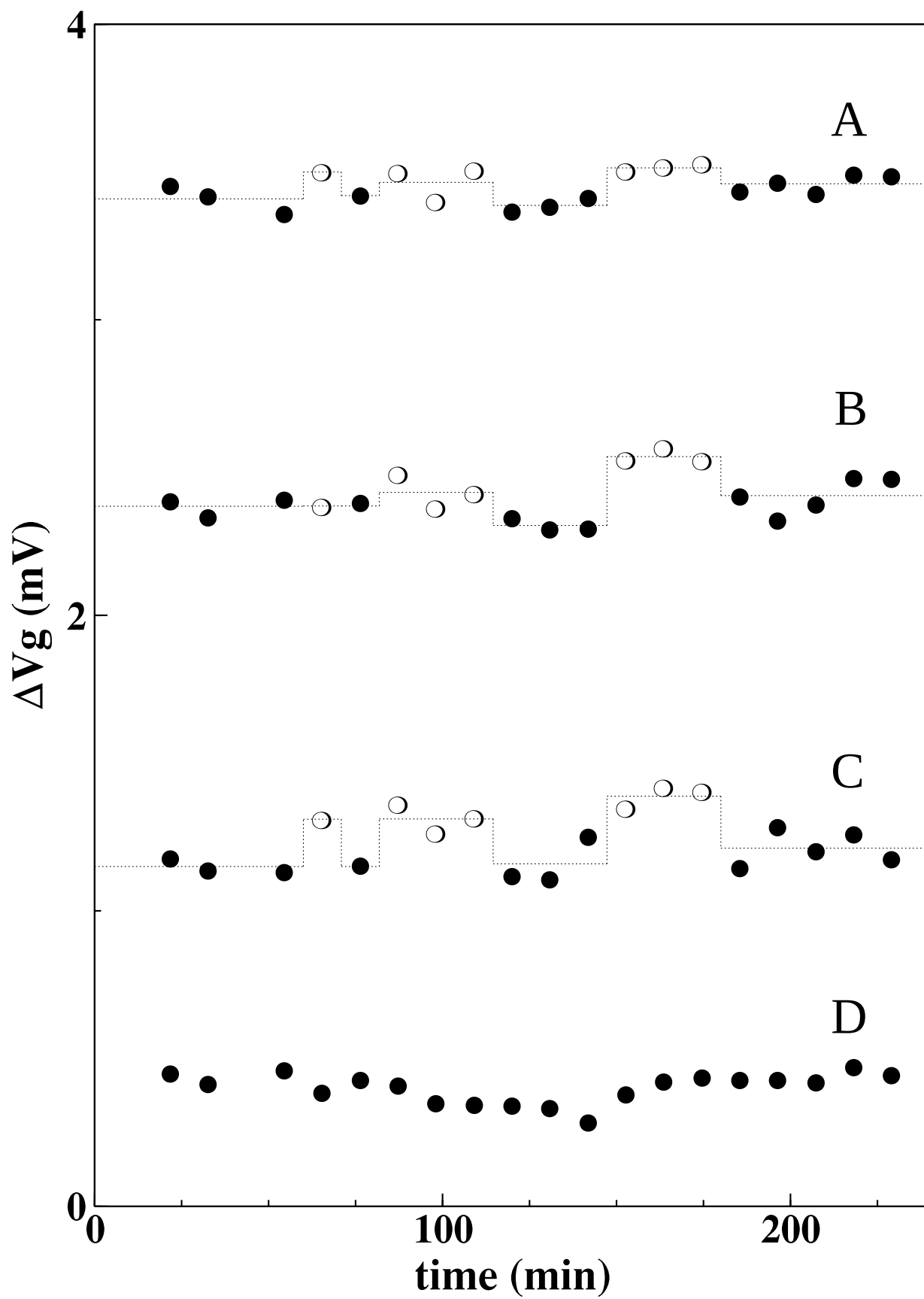


Fig.3, b